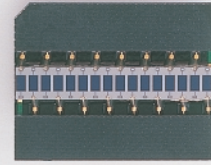


16-element Si photodiode array

S5668 series



Photodiode array ideal for light detection in a long, narrow area

S5668 series is a 16-element Si photodiode linear array. Each element has an active area of 1.175 mm (width) × 2.0 mm (height) and is arrayed at an element pitch of 1.575 mm. The entire linear array is mounted on a 25.4 mm (1 inch) long PC board. By linearly arranging two or more pieces of S5668 series, a long and narrow photodiode array can be easily configured at the same element pitch. For X-ray detection applications, S5668-11 with a CsI (TI) scintillator and S5668-34 with a ceramic scintillator are also available.

Features

- Active area: 1.175 × 2.0 mm per element
- Element pitch: 1.575 mm
- Mounted on a 1-inch (25.4 mm) long PC board
- Long and narrow format by multiple arrays
- High-speed response (S5668-02)
- Low capacitance (S5668-05)

Applications

- X-ray baggage inspection
- Multichannel spectrophotometry
- Optical position detection

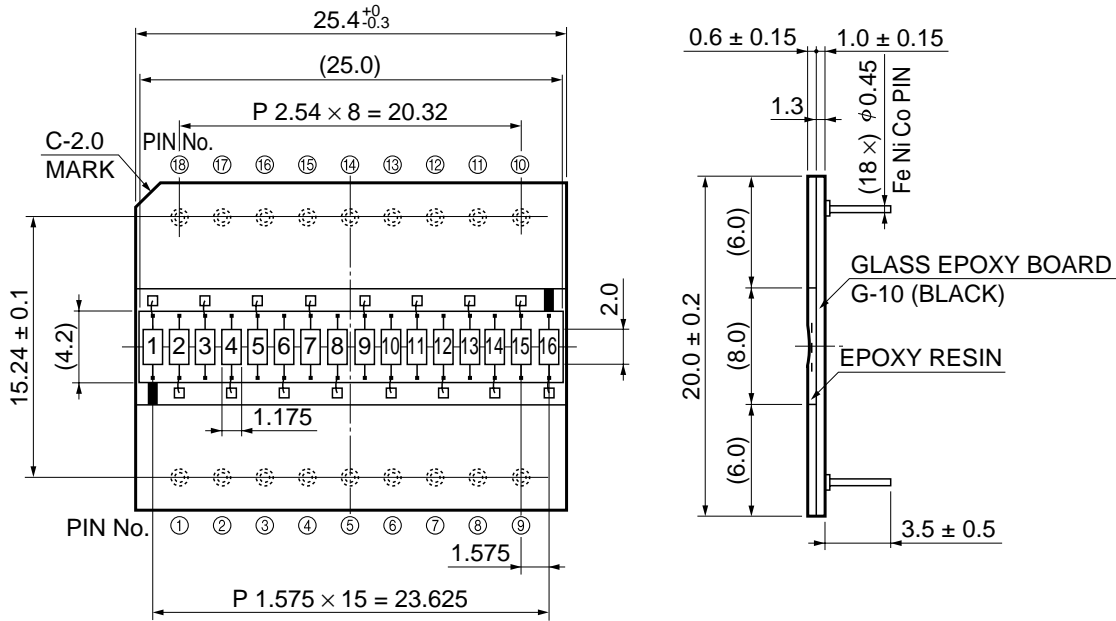
■ Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage	VR Max.	10	V
Operating temperature	Topr	-20 to +60	°C
Storage temperature	Tstg	-20 to +80	°C

■ Electrical and optical characteristics (Ta=25 °C, per 1 element)

Parameter	Symbol	Condition	S5668-01		S5668-02		S5668-05		Unit
			Typ.	Max.	Typ.	Max.	Typ.	Max.	
Spectral response range	λ		320 to 1100	-	320 to 1100	-	320 to 1060	-	nm
Peak sensitivity wavelength	λ_p		960	-	960	-	920	-	nm
Photo sensitivity	S	$\lambda=540$ nm	0.31	-	0.31	-	0.31	-	A/W
		$\lambda=\lambda_p$	0.56	-	0.58	-	0.56	-	
Dark current	ID	VR=10 mV	1	10	5	30	10	50	pA
Rise time	tr	VR=0 V RL=1 k Ω 10 to 90 %	0.7	-	0.1	-	0.1	-	μ s
Terminal capacitance	Ct	VR=0 V f=10 kHz	300	550	30	40	20	30	pF
Noise equivalent power	NEP	VR=0 V $\lambda=540$ nm	4.1×10^{-15}	-	9.3×10^{-15}	-	1.3×10^{-14}	-	W/Hz ^{1/2}

■ Dimensional outline (unit: mm)



①	CATHODE COMMON
②	ANODE 2
③	ANODE 4
④	ANODE 6
⑤	ANODE 8
⑥	ANODE 10
⑦	ANODE 12
⑧	ANODE 14
⑨	ANODE 16
⑩	CATHODE COMMON
⑪	ANODE 15
⑫	ANODE 13
⑬	ANODE 11
⑭	ANODE 9
⑮	ANODE 7
⑯	ANODE 5
⑰	ANODE 3
⑱	ANODE 1

KMPDA0042EB

HAMAMATSU

Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions. Specifications are subject to change without notice. No patent rights are granted to any of the circuits described herein. ©2006 Hamamatsu Photonics K.K.

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184, www.hamamatsu.com

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741